

# FS10AS-06

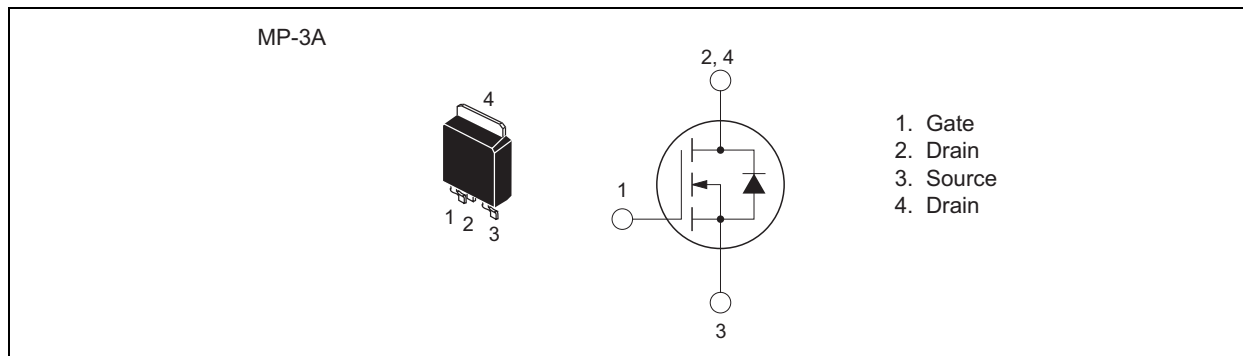
High-Speed Switching Use  
Nch Power MOS FET

REJ03G0240-0100  
Rev.1.00  
Aug.20.2004

## Features

- Drive voltage : 10 V
- $V_{DSS}$  : 60 V
- $r_{DS(ON)(max)}$  : 78 m $\Omega$
- $I_D$  : 10 A
- Recovery Time of the Integrated Fast Recovery Diode (TYP.) : 55 ns

## Outline



## Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

## Maximum Ratings

( $T_c = 25^\circ\text{C}$ )

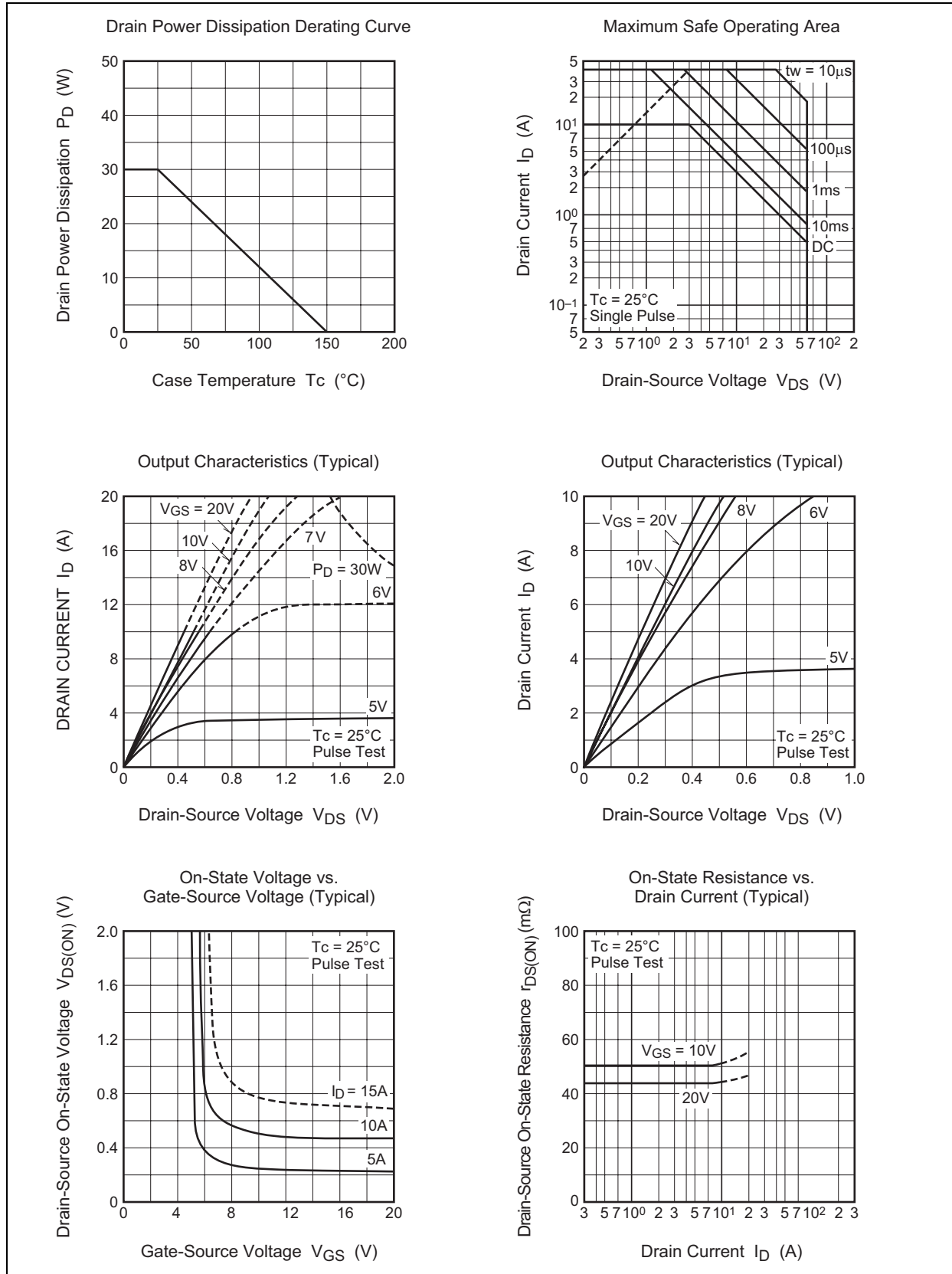
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	$V_{DSS}$	60	V	$V_{GS} = 0\text{ V}$
Gate-source voltage	$V_{GSS}$	$\pm 20$	V	$V_{DS} = 0\text{ V}$
Drain current	$I_D$	10	A	
Drain current (Pulsed)	$I_{DM}$	40	A	
Avalanche current (Pulsed)	$I_{DA}$	10	A	$L = 100\ \mu\text{H}$
Source current	$I_S$	10	A	
Source current (Pulsed)	$I_{SM}$	40	A	
Maximum power dissipation	$P_D$	30	W	
Channel temperature	$T_{ch}$	- 55 to +150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	- 55 to +150	$^\circ\text{C}$	
Mass	—	0.32	g	Typical value

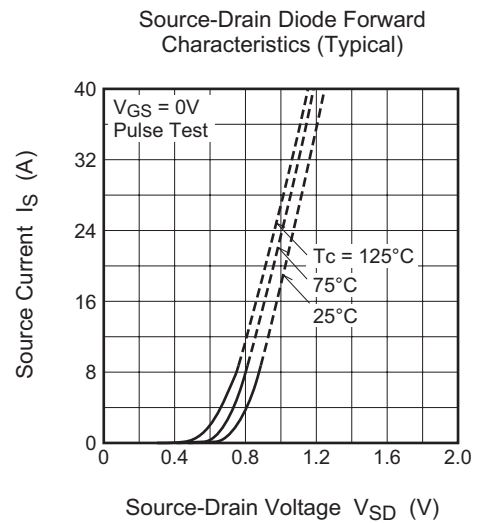
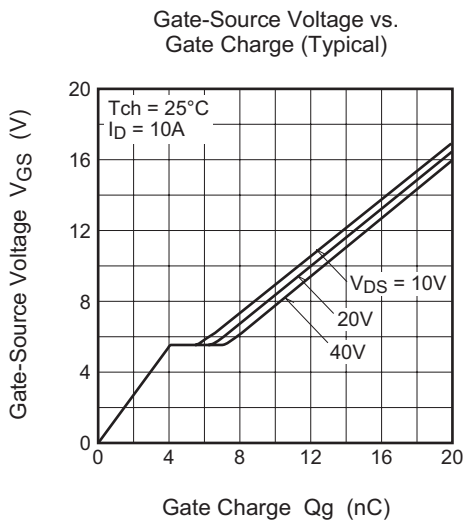
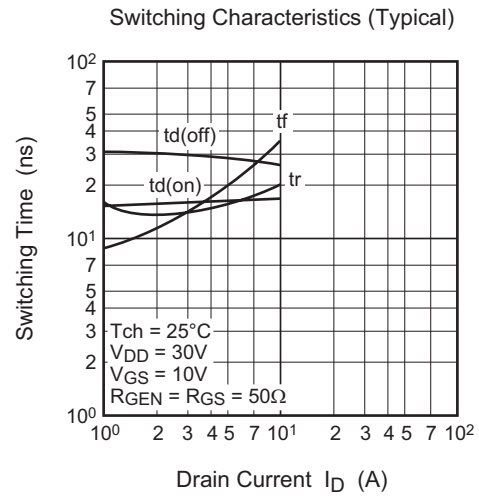
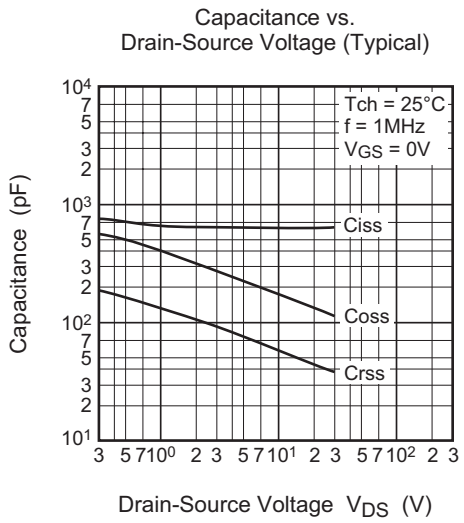
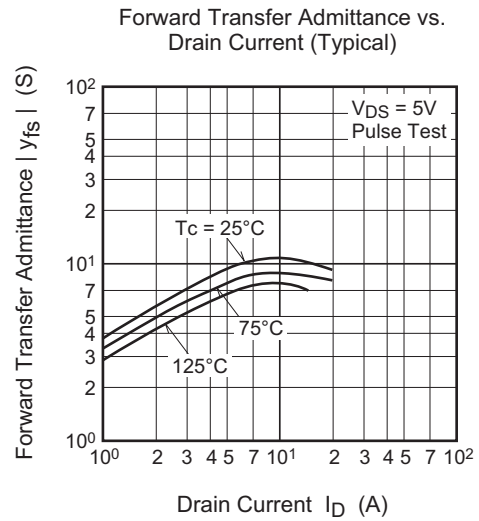
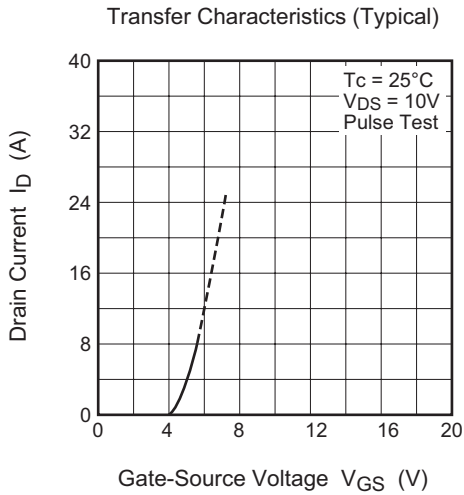
## Electrical Characteristics

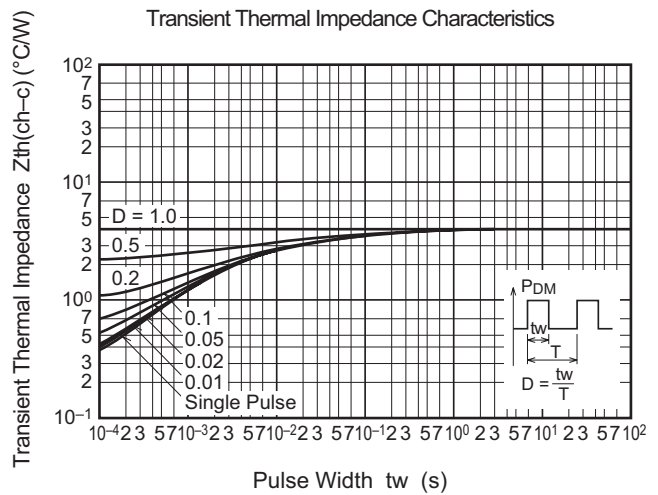
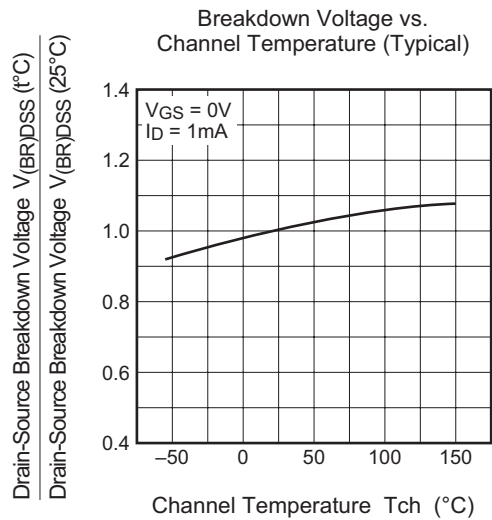
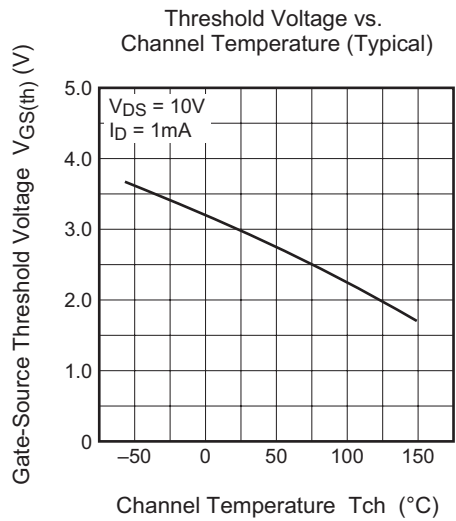
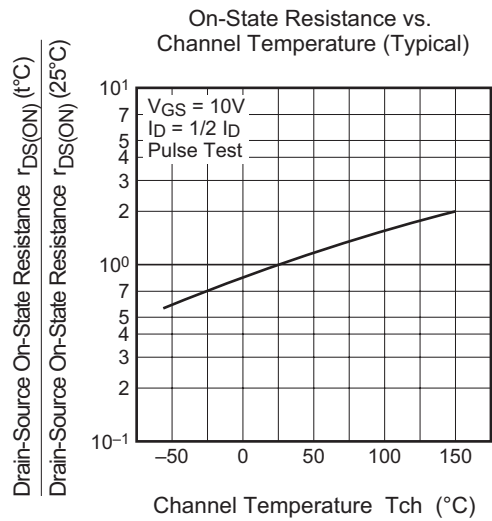
(T<sub>ch</sub> = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	60	—	—	V	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V
Gate-source leakage current	I <sub>GSS</sub>	—	—	±0.1	μA	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V
Drain-source leakage current	I <sub>DSS</sub>	—	—	0.1	mA	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V
Gate-source threshold voltage	V <sub>GS(th)</sub>	2.0	3.0	4.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Drain-source on-state resistance	r <sub>DS(ON)</sub>	—	58	78	mΩ	I <sub>D</sub> = 5 A, V <sub>GS</sub> = 10 V
Drain-source on-state voltage	V <sub>DS(ON)</sub>	—	0.29	0.39	mV	I <sub>D</sub> = 5 A, V <sub>GS</sub> = 10 V
Forward transfer admittance	y <sub>fs</sub>	—	9.0	—	S	I <sub>D</sub> = 5 A, V <sub>DS</sub> = 5 V
Input capacitance	C <sub>iss</sub>	—	600	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1MHz
Output capacitance	C <sub>oss</sub>	—	180	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	60	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	18	—	ns	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 5 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = R <sub>GS</sub> = 50 Ω
Rise time	t <sub>r</sub>	—	22	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	30	—	ns	
Fall time	t <sub>f</sub>	—	17	—	ns	
Source-drain voltage	V <sub>SD</sub>	—	1.0	1.5	V	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 0 V
Thermal resistance	R <sub>th(ch-c)</sub>	—	—	4.17	°C/W	Channel to case
Reverse recovery time	t <sub>rr</sub>	—	55	—	ns	I <sub>S</sub> = 10 A, dis/dt = -100 A/μs

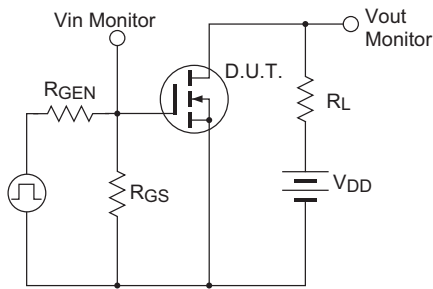
Performance Curves



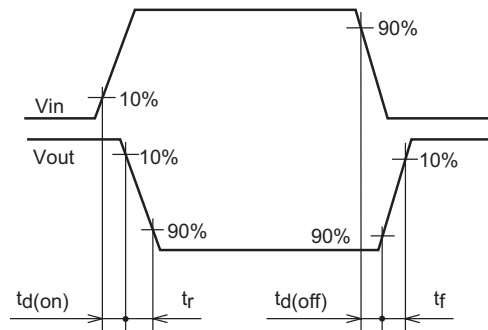




Switching Time Measurement Circuit



Switching Waveform



## Package Dimensions

**MP-3A**

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	0.32	Cu alloy

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A <sub>1</sub>	—	—	—
A <sub>2</sub>	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y <sub>1</sub>	—	—	—
ZD	—	—	—
ZE	—	—	—

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

## Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS10AS-06-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS10AS-06

Note : Please confirm the specification about the shipping in detail.

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